

Transistors

4V Drive Pch MOS FET

RSR025P03

●Structure

Silicon P-channel MOS FET

●Features

- 1) Low On-resistance
- 2) Space saving—small surface mount package (TSMT3)
- 3) 4V drive

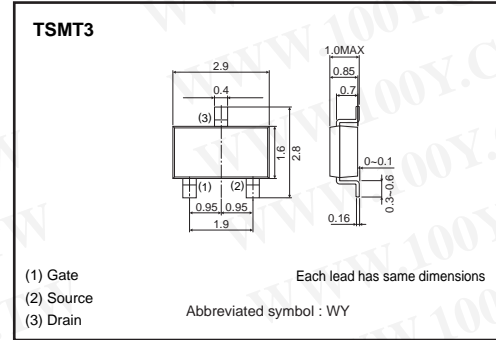
●Applications

Switching

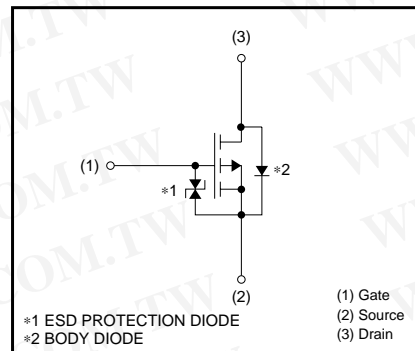
●Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
RSR025P03		○

●External dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	V _{DSS}	-30	V	
Gate-source voltage	V _{GSS}	±20	V	
Drain current	Continuous	I _D	±2.5	A
	Pulsed	I _{DP} *1	±10	A
Source current (Body diode)	Continuous	I _S	-0.8	A
	Pulsed	I _{SP} *1	-10	A
Total power dissipation	P _D *2	1	W	
Channel temperature	T _{ch}	150	°C	
Range of storage temperature	T _{stg}	-55 to +150	°C	

*1 Pw≤10μs, Duty cycle≤1%
 *2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	R _{th(ch-a)} *	125	°C/W

* Mounted on a ceramic board

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	–	–	±10	μA	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	–30	–	–	V	I _D =–1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	–	–	–1	μA	V _{DS} =–30V, V _{GS} =0V
Gate threshold voltage	V _{GS(th)}	–1.0	–	–2.5	V	V _{DS} =–10V, I _D =–1mA
Static drain-source on-state resistance	R _{DS(on)} *	–	70	98	mΩ	I _D =–2.5A, V _{GS} =–10V
		–	100	140	mΩ	I _D =–1.2A, V _{GS} =–4.5V
		–	115	160	mΩ	I _D =–1.2A, V _{GS} =–4V
Forward transfer admittance	Y _{fs} *	1.6	–	–	S	V _{DS} =–10V, I _D =–1.2A
Input capacitance	C _{iss}	–	460	–	pF	V _{DS} =–10V
Output capacitance	C _{oss}	–	105	–	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	–	65	–	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	–	10	–	ns	V _{DD} ≐–15V
Rise time	t _r *	–	10	–	ns	I _D =–1.2A
Turn-off delay time	t _{d(off)} *	–	42	–	ns	V _{GS} =–10V
Fall time	t _f *	–	10	–	ns	R _L =12.5Ω R _G =10Ω
Total gate charge	Q _g *	–	5.4	–	nC	V _{DD} ≐–15V V _{GS} =–5V
Gate-source charge	Q _{gs} *	–	1.4	–	nC	I _D =–2.5A
Gate-drain charge	Q _{gd} *	–	1.6	–	nC	R _L =6Ω R _G =10Ω

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{SD}	–	–	–1.2	V	I _S =–0.8A, V _{GS} =0V

Appendix

Notes

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